

# 深圳市晶泰源电子有限公司

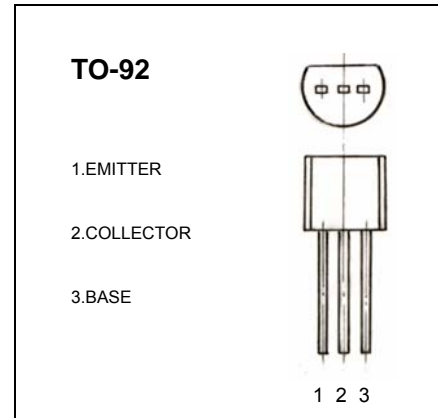
## 8050S TRANSISTOR (NPN)

### FEATURES

- Complimentary to 8550S
- Collector current:  $I_C=0.5A$

### MAXIMUM RATINGS ( $T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	40	V
$V_{CEO}$	Collector-Emitter Voltage	25	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current -Continuous	0.5	A
$P_C$	Collector Power Dissipation	0.625	W
$T_J$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature	-55-150	$^{\circ}C$



### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1mA, I_B=0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=40V, I_E=0$			0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE}=20V, I_B=0$			0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=1V, I_C=50mA$	85		400	
	$h_{FE(2)}$	$V_{CE}=1V, I_C=500mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=500mA, I_B=50mA$			1.2	V
Transition frequency	$f_T$	$V_{CE}=6V, I_C=20mA$ $f=30MHz$	150			MHz

### CLASSIFICATION OF $h_{FE(1)}$

Rank	C	D
Range	100-200	200-400